

AMENDMENTS TO SPECIFICATION

On Page 1, please insert the phrase, ", now U.S. Patent 6,477,479" after -- U.S. Patent Application No. 09/210,428" and please insert the phrase "now U.S. Patent 6,438,497," after U.S. Patent Application No. 09/210,086, such that the paragraph reads:

¶, The present application is related to co-pending U.S. Patent Application No. 09/210,428, now U.S. Patent 6,477,479 and U.S. Patent Application No. 09/210,086, now U.S. Patent 6,438,497, all filed on December 10, 1998 and incorporated herein by reference.

On Page 78, line 15, please insert the phrase "now U.S. Patent 6,393,895," after the year, "1998", such that the paragraph reads:

¶ 2 In this example, surface launched acoustic wave sensors can be fabricated on thin silicon-nitride or etched silicon membranes 174 similar to those described above. A piezoelectric material 176, such as zinc oxide, is then deposited as a thin layer on top of the membrane to produce an acoustic wave sensing device. The physical dimensions of the electrode, such as its thickness, size, and configuration, can be adjusted so that the electrode operates in, for example, a surface acoustic wave (SAW) resonance mode, a thickness shear mode (TSM), a flexural plate wave (FPW) resonance mode, or other resonance mode. When the electrode acts as a resonator, its resonating response is affected by, for example, the sample's viscosity and density. Copending U.S. Application No. 09/133,171 to Matsiev et al, filed August 12, 1998, now U.S. Patent 6,393,895, describes mechanical resonators in more detail and is incorporated by reference herein.